SSCL19P60GT4

P-Channel Enhancement Mode MOSFET

➢ Features

V_{DS}	V_{GS}	$R_{DS(ON)}$ Typ.	I_D
-60V	±20V	19mΩ@-10V	-67A
		25mΩ@-4.5V	

➢ Description

This device is P-Channel enhancement MOSFET. Uses SGT technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

100% UIS + ΔVDS + Rg Tested!

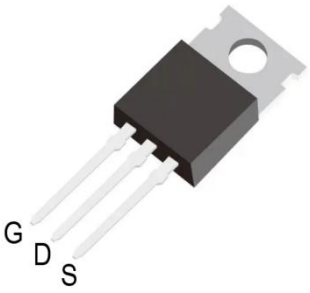
➢ Applications

- Load Switch
- PWM Application
- Power Management
- DC/DC Conversion

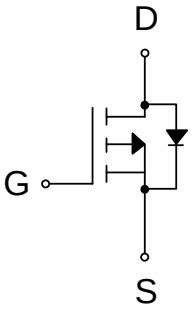
➢ Ordering Information

Device	Package	Shipping
SSCL19P60GT4	TO-220-3L	50/Tube

➢ Pin configuration



TO-220-3L (Top View)



Pin Configuration

Marking

(XXYY: Internal Traceability Code)

➢ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{DSS}	Drain-to-Source Voltage		-60	V
V_{GSS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current [d]	T_C=25℃	-67	A
		T_C=100℃	-42	
I_{DSM}	Continuous Drain Current [a]	T_A=25℃	-10	A
		T_A=70℃	-6.5	
I_{DM}	Pulsed Drain Current [b]		-268	A
P_D	Power Dissipation [c]	T_C=25℃	96	W
		T_C=100℃	38	
P_{DSM}	Power Dissipation [a]	T_A=25℃	2.3	W
		T_A=70℃	0.9	
I_{AS}	Avalanche Current [b] L=0.5mH Single Pulse		-20	A
E_{AS}	Avalanche Energy [b] L=0.5mH Single Pulse		100	mJ
T_J	Operation junction temperature		-55~150	℃
T_{STG}	Storage temperature range		-55~150	

➢ Thermal Resistance Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Max.	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance [a]	55	65	℃/W
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	1.3	1.7	

Note:

a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz.copper, in a still air environment with T_A=25℃.The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.

b. Repetitive rating, pulse width limited by junction temperature.

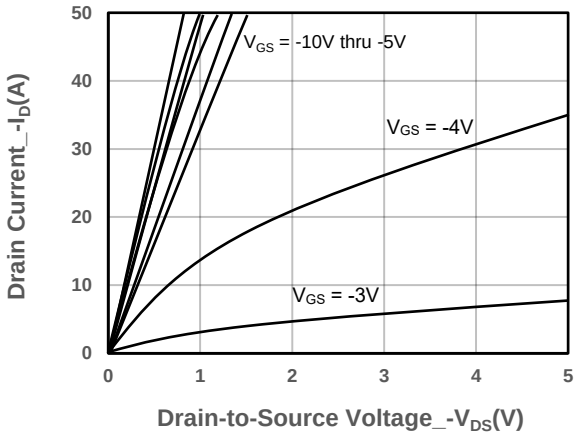
c. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

d. The maximum current rating is package limited.

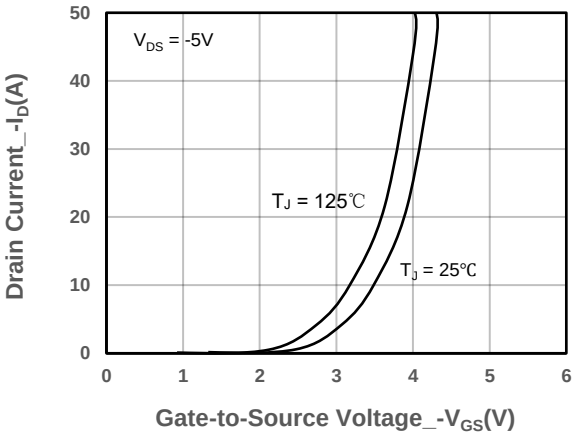
➢ Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250uA	-1	-1.8	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -20A		19	26	mΩ
		V_{GS} = -4.5V, I_D = -10A		25	33	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -60V, V_{GS} = 0V			-1	μA
Gate-Source Leak Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
Transconductance	G_{FS}	V_{DS} = -5V, I_D = -10A		18		S
Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = -10A		-0.8	-1.3	V
Gate Resistance	R_G	V_{DS} = 0V, f = 1MHz		7.8		Ω
Input Capacitance	C_{ISS}	V_{DS} = -30V, V_{GS} = 0V, f = 1MHz		1510		pF
Output Capacitance	C_{OSS}			250		
Reverse Transfer Capacitance	C_{RSS}			15		
Total Gate Charge	Q_G	V_{GS} = -10V, V_{DS} = -30V, I_D = -20A		23		nC
Gate to Source Charge	Q_{GS}			4		
Gate to Drain Charge	Q_{GD}			3.5		
Turn-on Delay Time	$T_{D(ON)}$	V_{GS} = -10V, V_{DS} = -30V, I_D = -20A, R_G = 3Ω,		14		ns
Rise Time	T_r			16		
Turn-off Delay Time	$T_{D(OFF)}$			41		
Fall Time	T_f			46		
Diode Recovery Time	T_{rr}	I_F=-20A, di/dt=100A/us		62		ns
Diode Recovery Charge	Q_{rr}	I_F=-20A, di/dt=100A/us		107		nC

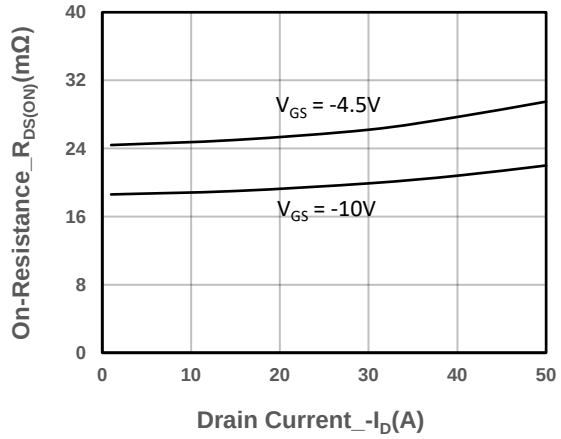
➢ Typical Performance Characteristics (T_A=25℃ unless otherwise noted)



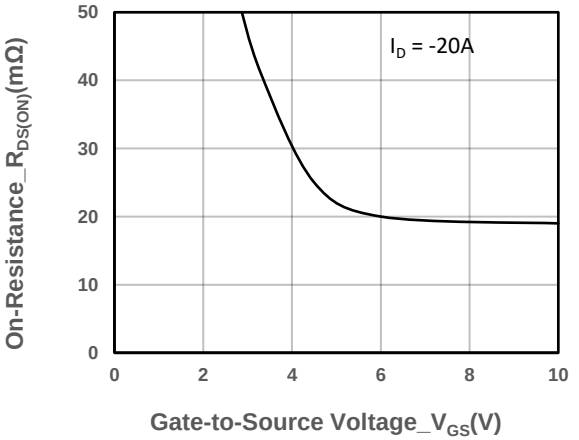
Output Characteristics



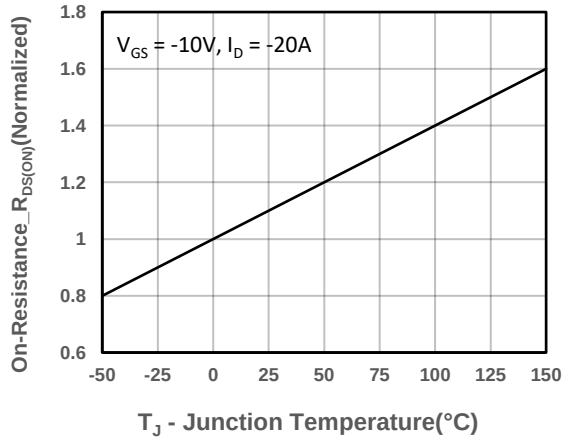
Transfer Characteristics



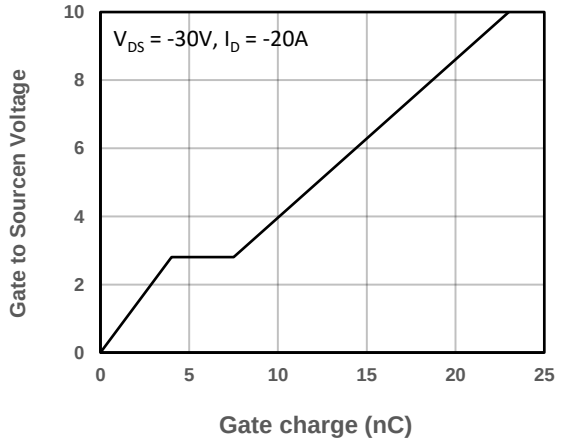
On-Resistance vs. Drain Current and Gate Voltage



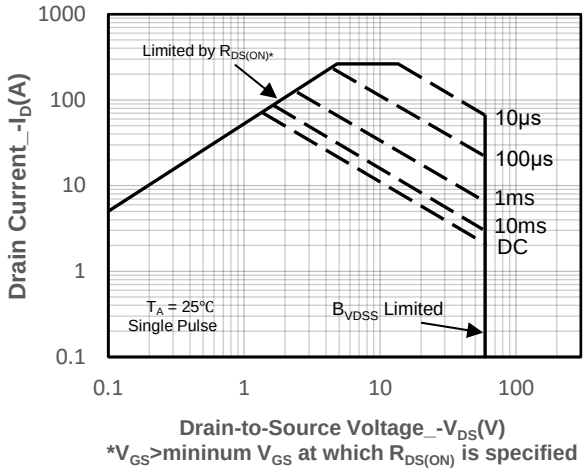
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature

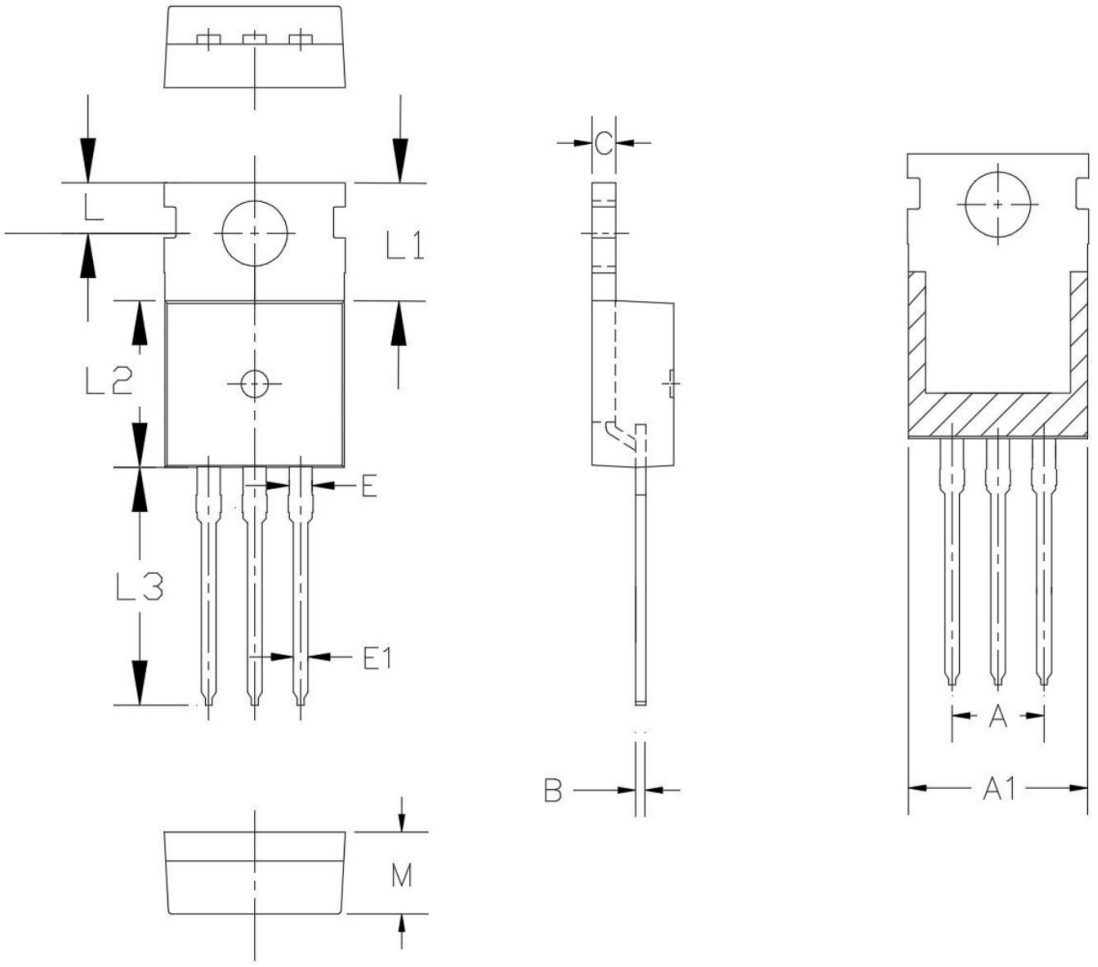


Gate-Source Voltage vs. Gate charge



Safe Operating Area vs. Junction-to-Ambient

➢ Package Information



Symbol	MILL IMETER		
	Min	Nom	Max
A		5.08 BSC	
A1	9.00	10.00	11.00
B	0.33	--	0.65
C	1.20	--	1.40
E	1.17	--	1.37
E1	0.60	--	1.10
L	2.50	--	3.00
L1	6.3	6.5	6.7
L2	8.95	--	9.75
L3	12.88	--	13.40
M	4.30	--	4.70

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